Author's Journal Publications

1. **R. Singh**, S. Mittal, and S. Verma, "Junctionless Accumulation-Mode SOI Ferroelectric FinFET for Synaptic Weights," in ***Microelectronics Journal***, vol. 153, pp. 106413, June. 2024, **doi: 10.1016/j.mejo.2024.106413**.

2. **R. Singh**, and S. Verma, "Memristive Ferroelectric FET for 1T-1R Nonvolatile Memory with Non-Destructive Readout", ***IEEE Open Journal of Nanotechnology***, vol. 6, pp. 27-34, Jan. 2025, **doi: 10.1109/OJNANO.2025.3531759**.

3. **R. Singh**, S. Verma and S. Mittal, "FinFET Fin-Trimming During Replacement Metal Gate for an Asymmetric Device Toward STT MRAM Performance Enhancement," in ***IEEE Transactions on Electron Devices***, vol. 69, no. 12, pp. 6699-6704, Dec. 2022, **doi: 10.1109/TED.2022.3217206**.

Author's Conference Publications

1. **Roopesh Singh**, Sumit Purkait, and Shivam Verma, "**Junction Less Ferroelectric FET on FDSOI for Non-Volatile Logic In-Memory Applications**," ***in Proc. 6th IEEE International Conference on Emerging Electronics (ICEE)***, Bengaluru, India, 11-14 December 2022.

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